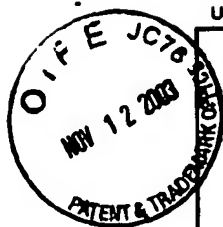




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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)			Application Number	10/077,784	
			Filing Date	February 20, 2002	
			First Named Inventor	Terry L. Gilton	
			Art Unit	2818	
			Examiner Name	Not Yet Assigned PHAN	
Sheet	1	of	8	Attorney Docket Number	M4065.0482/P482

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
TP	AA	5,761,115	06/02/1998	Kozicki et al.	
TP	AB	6,084,796	07/04/2000	Kozicki et al.	
TP	AC	5,914,893	06/22/1999	Kozicki et al.	
TP	AD	5,896,312	04/20/1999	Kozicki et al.	
TP	AE	6,388,324	05/14/2002	Kozicki et al.	
TP	AF	US 2002/0000666	01/03/2002	Kozicki et al.	
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TP	AJ	5,789,277	08/04/1998	Zahorik et al.	
TP	AK	6,348,365	02/19/2002	Moore et al.	
	AL				
	AM				
	AN				
	AO				

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>a</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>2</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
TP	BA	WO 02/21542	03/14/2002	Kozicki et al.		
TP	BB	WO 00/48196	08/17/2000	Kozicki et al.		
TP	BC	WO 97/48032	12/18/1997	Kozicki et al.		
TP	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	Trong Phan	Date Considered	1/22/04
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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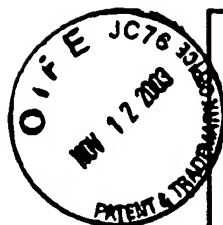
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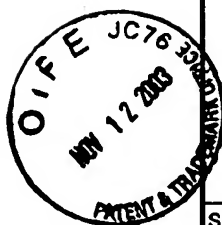




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		Filing Date	February 20, 2002
		First Named Inventor	Terry L. Gilton
		Group Art Unit	2818
		Examiner Name	Not Yet Assigned PHAN
		Attorney Docket Number	M4065.0482/P482
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Application Number	10/077,784
Filing Date	February 20, 2002
First Named Inventor	Terry L. Gilton
Group Art Unit	2818
Examiner Name	Not Yet Assigned PHAN
Attorney Docket Number	M4065.0482/P482

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**Examiner  
Signature**

Trong Phan

Date Considered

1/22/04

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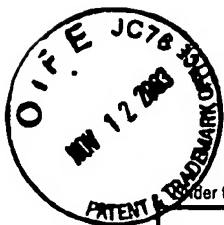
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				Application Number	10/077,784
				Filing Date	February 20, 2002
				First Named Inventor	Gilton, et al.
				Art Unit	2818
				Examiner Name	T. Phan
Sheet	1	of	4	Attorney Docket Number	M4065.0482/P482

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				First Named Inventor	Gilton, et al.
				Art Unit	2818
				Examiner Name	T. Phan
Sheet	2	of	4	Attorney Docket Number	M4065.0482/P482

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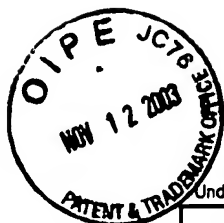
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TP	BA	56126916		10/19981	Akira et al.		

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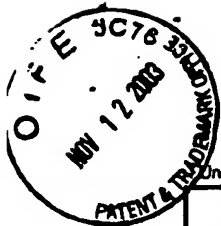
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				Examiner Name	T. Phan
Sheet	4	of	4	Attorney Docket Number	M4065.0482/P482

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
TP	CA	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: <i>Programmable Metalization Cell(PMC)</i> , pp. 1-6 (Pre-May 2000).	
	CB	Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 24-29 (1982).	
	CC	Hilt, DISSERTATION: <i>Materials characterization of Silver Chalcogenide Programmable Metalization</i>	
	CD	Hirose et al., <i>High Speed Memory Behavior and Reliability of an Amorphous As<sub>2</sub>S<sub>3</sub> Film Doped Ag</i> , PHYS. STAT. SOL. (a) 61, pp. 87-90 (1980).	
	CE	Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAM. SOC., No. 3-4, pp. 183-188 (March-April 1979).	
	CF	Huggett et al., Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF <sub>6</sub> , 42 Appl. Phys. Lett., No. 7, pp. 592-594 (April 1983).	
	CG	Kawaguchi et al., <i>Mechanism of photosurface deposition</i> , 164-166 J. NON-CRYST. SOLIDS, pp. 1231-1234 (1993).	
	CH	Kolobov et al., Photodoping of amorphous chalcogenides by metals, Advances in Physics, 1991, Vol. 40, No. 5, pgs. 625-684.	
	CI	Kozicki et al., Silver incorporation in thin films of selenium rich Ge-Se glasses, International Congress on Glass, Volume 2, Extended Abstracts, July 2001, pgs. 8-9.	
	CJ	Michael N. Kozicki, 1. Programmable Metalization Cell Technology Description, February 18, 2000	
	CK	Michael N. Kozicki, Axon Technologies Corp. and Arizona State University, Presentation to Micron Technology, Inc., April 6, 2000	
	CL	Kozicki et al., Applications of Programmable Resistance Changes In Metal-Doped Chalcogenides, Electrochemical Society Proceedings, Volume 99-13, 1999, pgs. 298-309.	
	CM	Kozicki et al., Nanoscale effects in devices based on chalcogenide solid solutions, Superlattices and Microstructures, Vol. 27, No. 516, 2000, pgs. 485-488.	
	CN	Kozicki et al., Nanoscale phase separation in Ag-Ge-Se glasses, Microelectronic Engineering 63 (2002) pgs 155-159.	
	CO	McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects o electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f	
↓	CP	Owens et al., Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures, Nanostructure Physics and Fabrication, pp. 447-451 (M. Reed ed. 1989).	
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Examiner Signature	Trong Phan	Date Considered	1/22/04
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<b>Substitute for form 1449A/PTO</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/077,784
				Filing Date	February 20, 2002
				First Named Inventor	Terry L. Gilton
				Art Unit	2818
				Examiner Name	Not Yet Assigned PHAN
Sheet	1	of	1	Attorney Docket Number	M4065.0482/P482

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.†	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code* (if known)			
TP	AA	6,469,364-B1	10-22-2002	Kozicki	
TP	AB	2002/0168820-A1	11-14-2002	Kozicki et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
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